TOSHIBA

MICROWAVE SEMICONDUCTOR

TECHNICAL DATA

MICROWAVE POWER GaAs FET

TIM5964-4A

FEATURES:

- HIGH POWER
  P_{1dB} = 36.5 dBm at 5.9 GHz to 6.4 GHz
- HIGH GAIN
  G_{1dB} = 8.5 dB at 5.9 GHz to 6.4 GHz
- BROAD BAND INTERNALLY MATCHED
- HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS (Ta = 25℃)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1 dB Compression Point	P_{1dB}	V_{DS} = 10V f = 5.9～6.4GHz	dBm	36.0	36.5	-
Power Gain at 1 dB Compression Point	G_{1dB}		dB	8.0	8.5	-
Drain Current	I_{DS}		A	-	1.1	1.5
Power Added Efficiency	η add		%	-	35	-
Channel Temperature Rise	$\triangle T_{ch}$	$V_{DS} \times I_{DS} \times R_{th(c-c)}$	℃	-	-	80

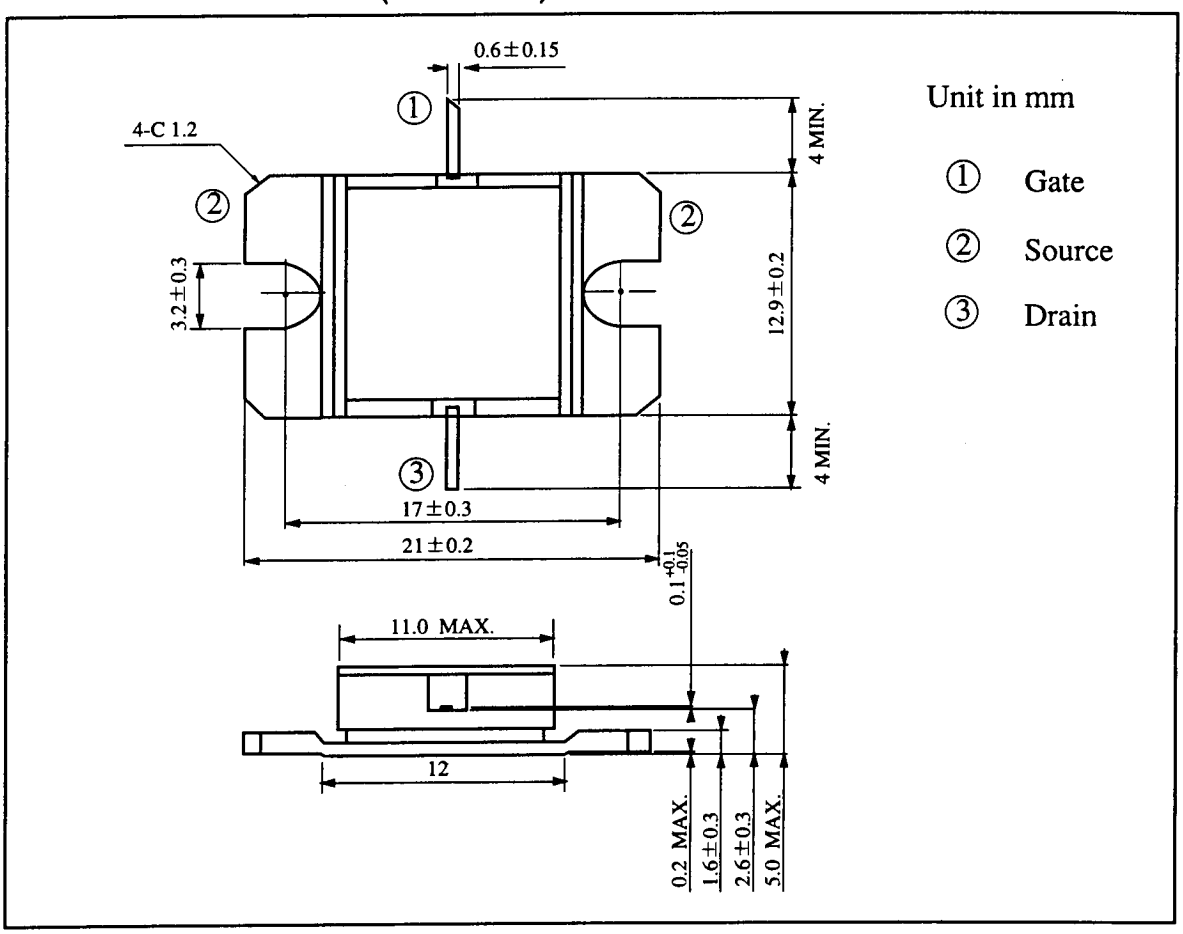
ELECTRICAL CHARACTERISTICS (Ta = 25℃)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Trans-conductance	gm	V_{DS} = 3V I_{DS} = 1.5A	ms	-	900	-
Pinch-off Voltage	VGSoff	V_{DS} = 3V I_{DS} = 20mA	V	-2.0	-3.5	-5.0
Saturated Drain Current	I_{DSS}	V_{DS} = 3V V_{GS} = 0V	A	-	2.9	3.8
Gate-Source Breakdown Voltage	V_{GSO}	I_{GS} = -60μA	V	-5	-	-
Thermal Resistance	$R_{th(c-c)}$	Channel to Case	℃/W	-	4.0	6.0

ABSOLUTE MAXIMUM RATINGS (Ta = 25℃)

CHARACTERISTIC	SYMBOL	UNIT	RATING
Drain=Source Voltage	V_{DS}	V	15
Gate=Source Voltage	V_{GS}	V	-5
Drain Current	I_{DS}	A	4
Total Power Dissipation (Tc=25℃)	P_T	W	20
Channel Temperature	T_{ch}	℃	175
Storage Temperature	T_{stg}	℃	-65~175

PACKAGE OUTLINE (2-11D1B)

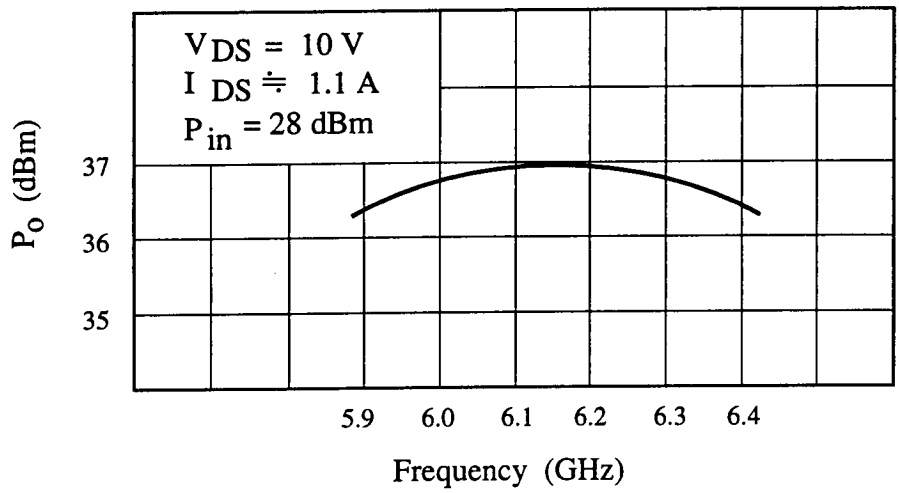


HANDLING PRECAUTIONS FOR PACKAGED TYPE

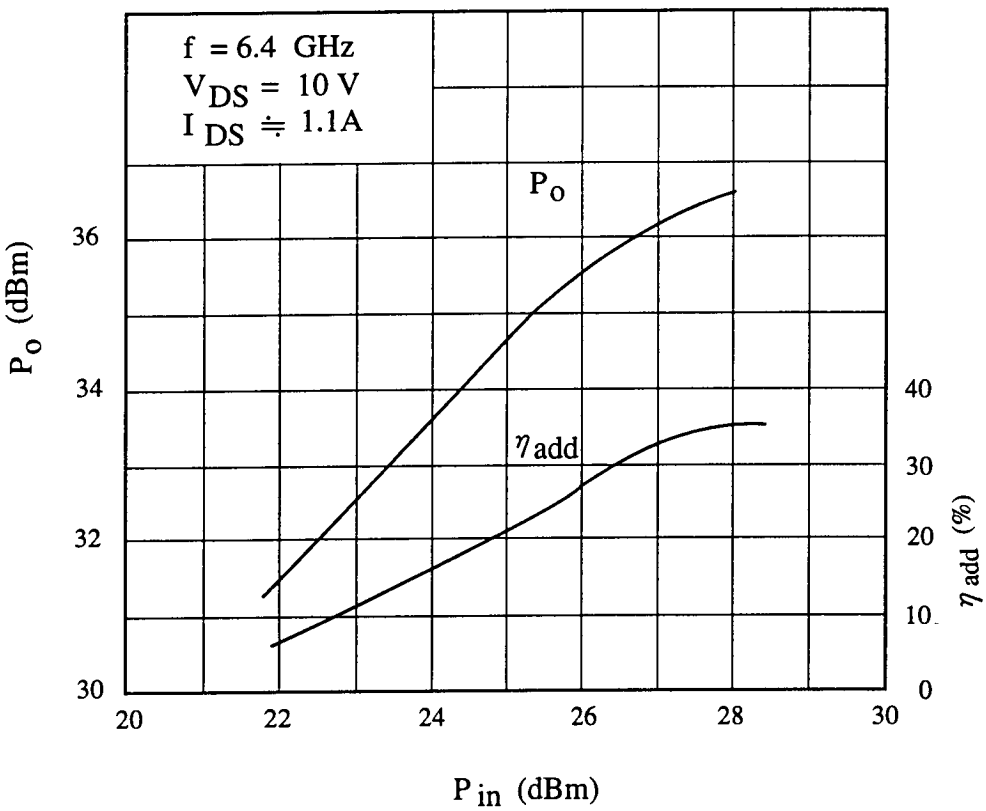
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260℃.

RF PERFORMANCES

Output Power vs. Frequency



Output Power vs. Input Power



POWER DISSIPATION VS. CASE TEMPERATURE